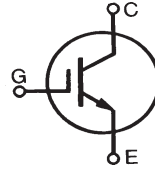


1000V XPT™ GenX4™ IGBT

IXYA24N100C4HV IXYP24N100C4

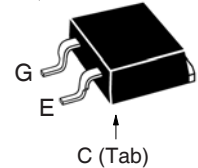
High Speed IGBT
for 20-50kHz Switching



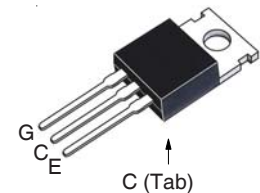
$$\begin{aligned} V_{CES} &= 1000V \\ I_{C110} &= 24A \\ V_{CE(sat)} &\leq 2.3V \\ t_{fi(typ)} &= 40ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	1000	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	76	A
I_{C110}	$T_C = 110^\circ C$	24	A
I_{CM}	$T_C = 25^\circ C$, 1ms	132	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 48$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 660V$, $T_J = 150^\circ C$ $R_G = 50\Omega$, Non Repetitive	8	μs
P_C	$T_C = 25^\circ C$	375	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d F_C	Mounting Torque (TO-220) Mounting Force (TO-263HV)	1.13/10 10..65 / 22..14.6	Nm/lb.in N/lb
Weight	TO-263HV TO-220	2.5 3.0	g g

TO-263HV
(IXYA..HV)



TO-220
(IXYP)



G = Gate D = Collector
e = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Positive Thermal Coefficient of $V_{ce(sat)}$
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1000		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			25 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 24A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.86 2.30	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 24\text{A}, V_{CE} = 10\text{V}$, Note 1	8	13	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		880	pF
C_{oes}			62	pF
C_{res}			35	pF
$Q_{g(on)}$	$I_C = 24\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		43	nC
Q_{ge}			8	nC
Q_{gc}			20	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 24\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2		15	ns
t_{ri}			43	ns
E_{on}			3.6	mJ
$t_{d(off)}$			147	ns
t_{fi}			40	ns
E_{off}			1.0	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 24\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2		15	ns
t_{ri}			35	ns
E_{on}			4.2	mJ
$t_{d(off)}$			190	ns
t_{fi}			53	ns
E_{off}			1.6	mJ
R_{thJC}	TO-220			0.40 $^\circ\text{C/W}$
R_{thCS}		0.50		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

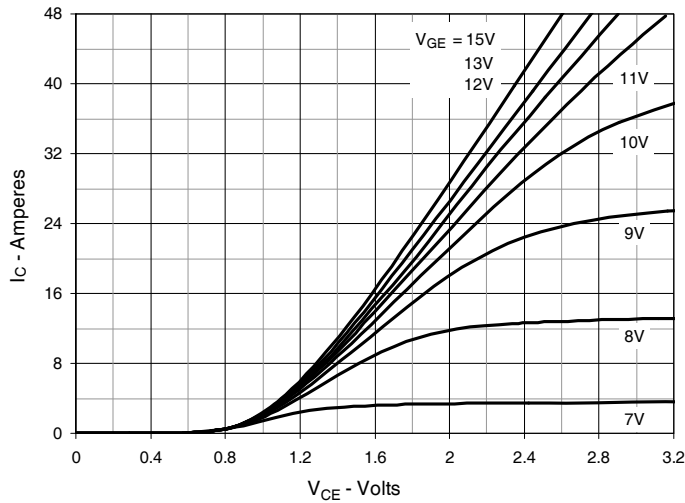
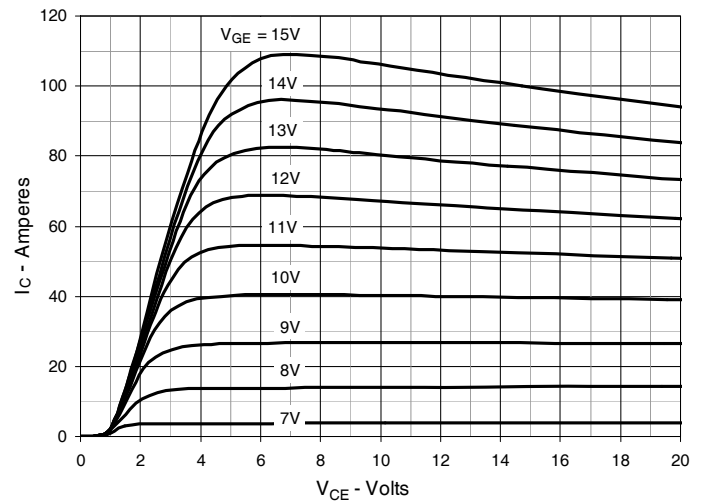
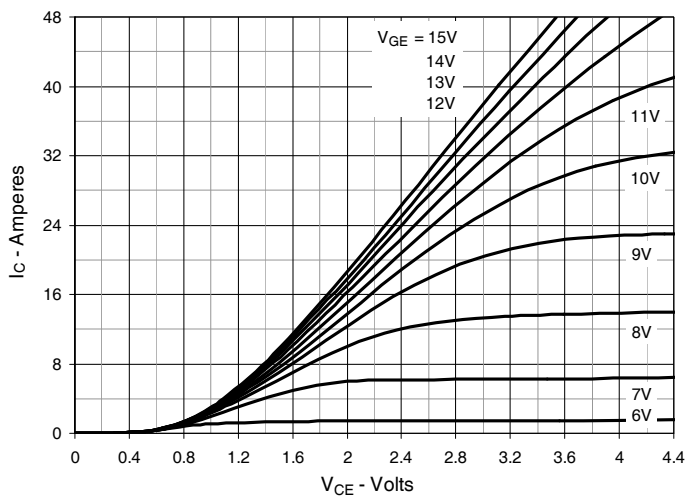
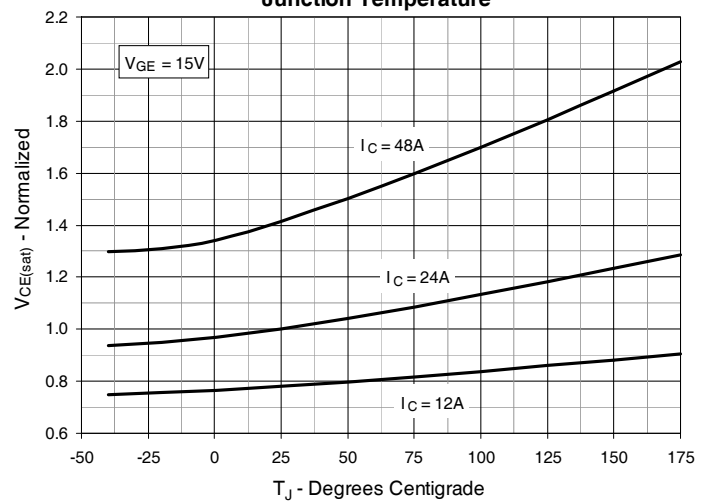
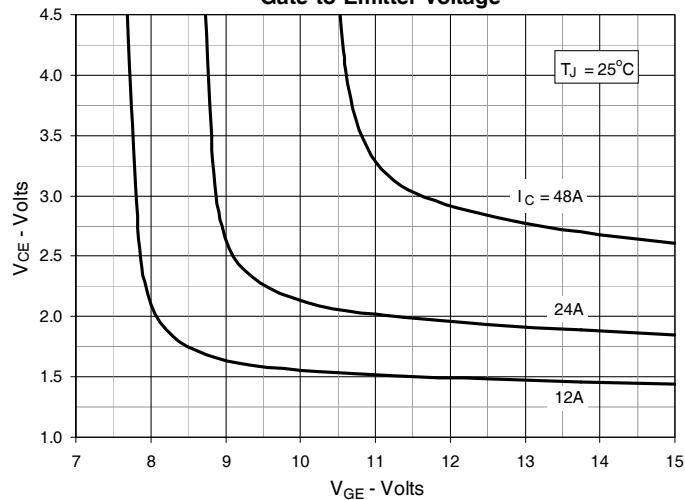
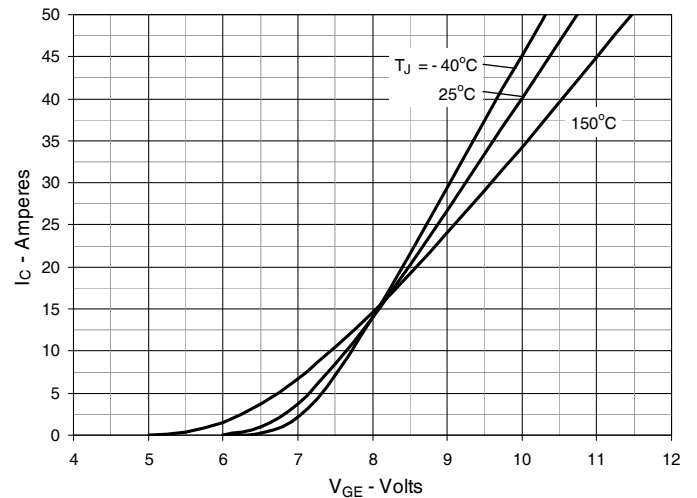
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

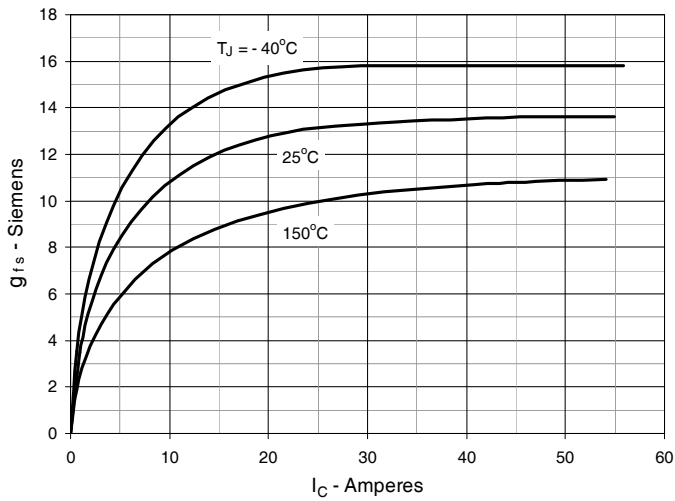


Fig. 8. Gate Charge

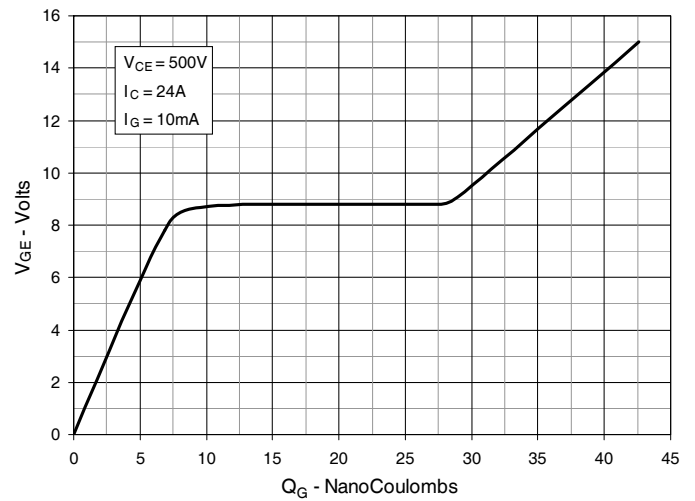


Fig. 9. Capacitance

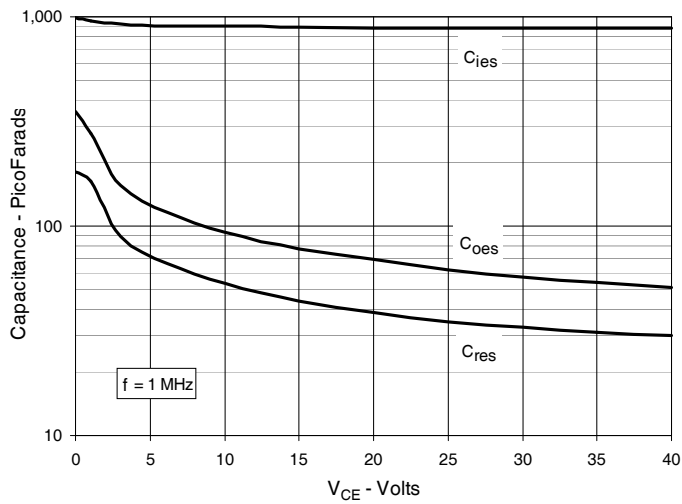


Fig. 10. Reverse-Bias Safe Operating Area

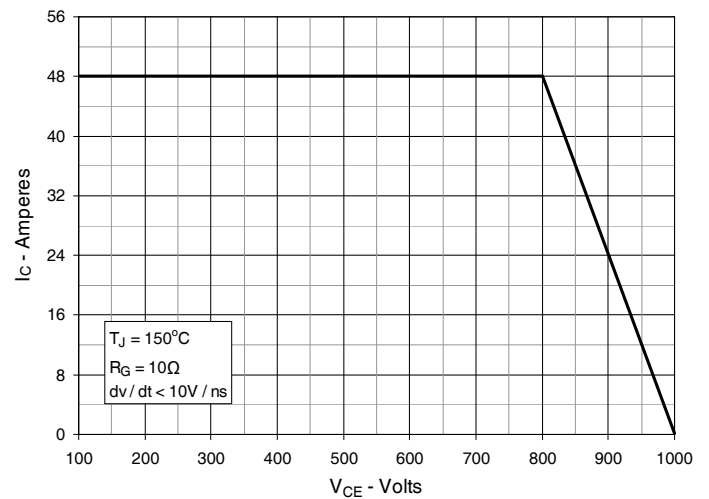


Fig. 11. Maximum Transient Thermal Impedance

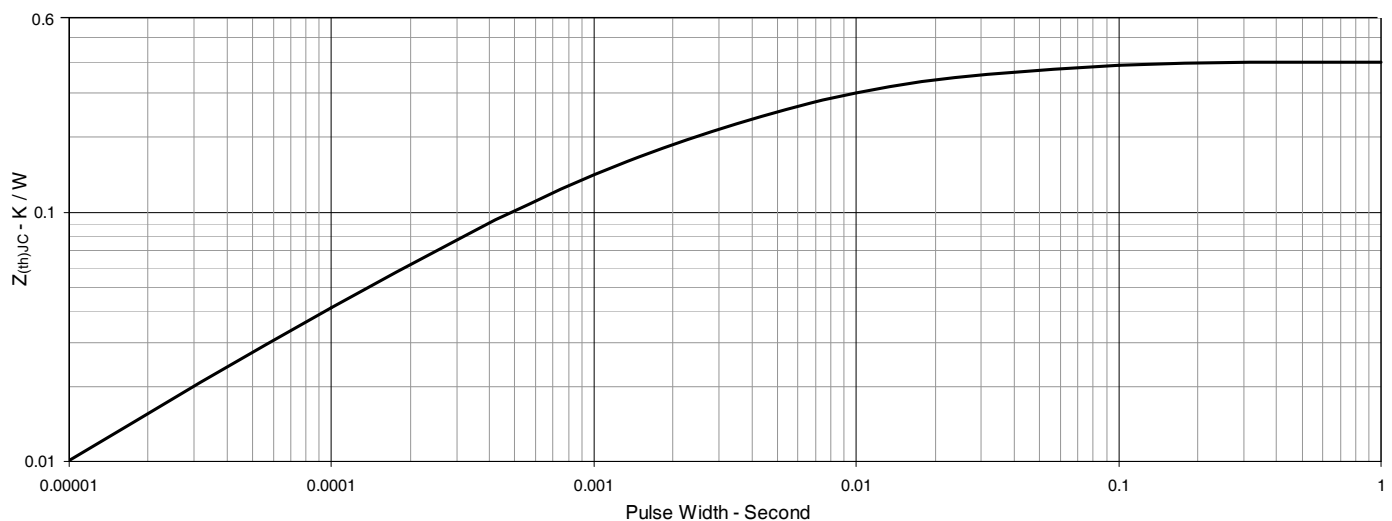


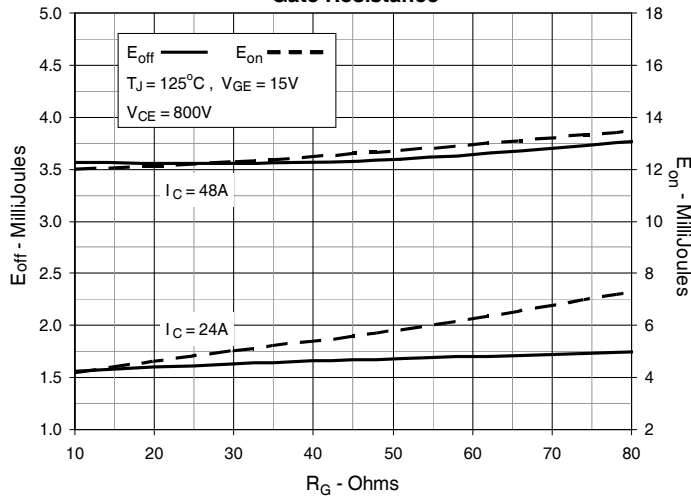
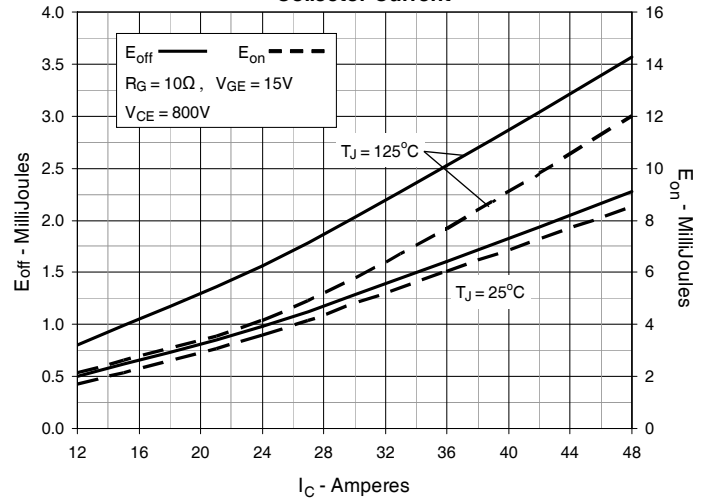
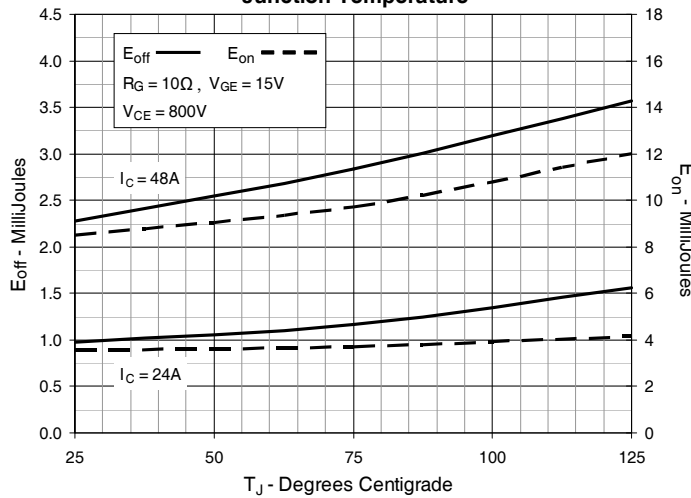
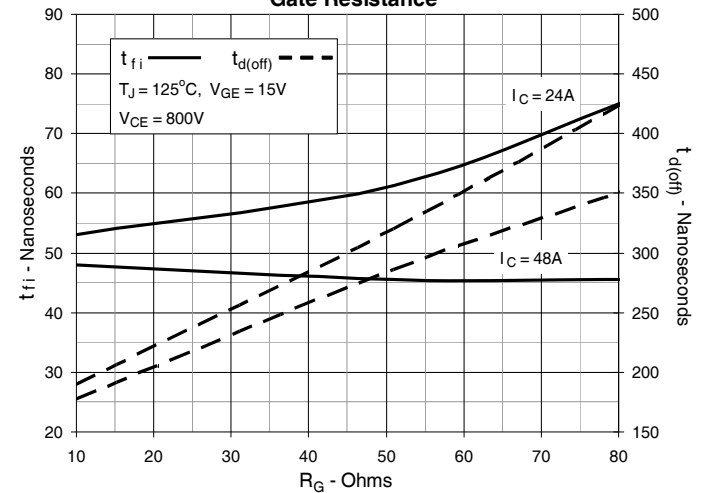
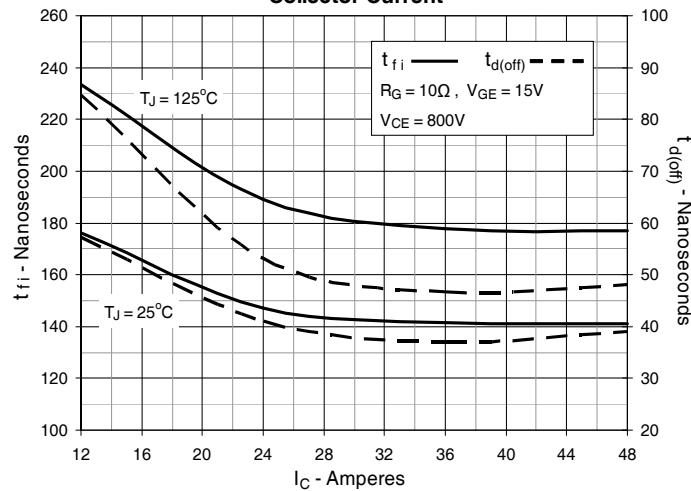
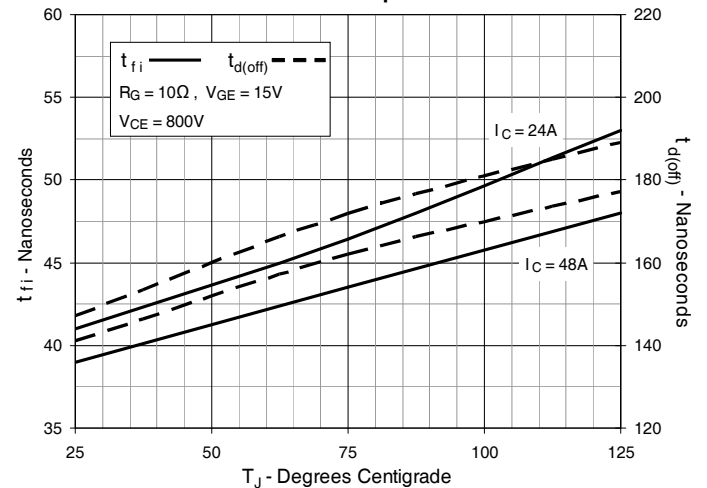
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

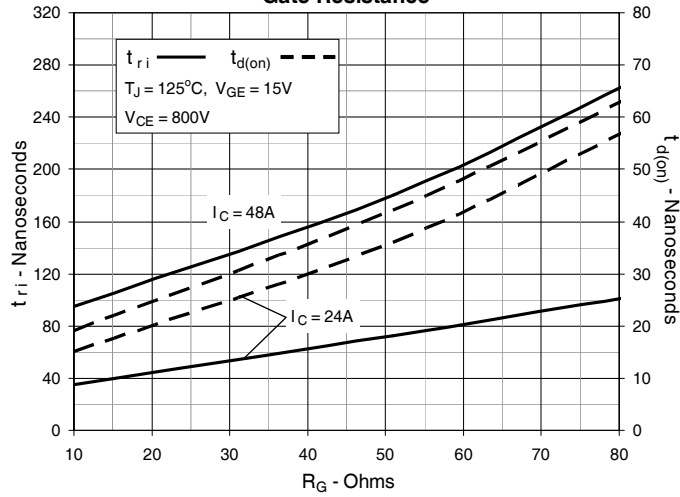


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

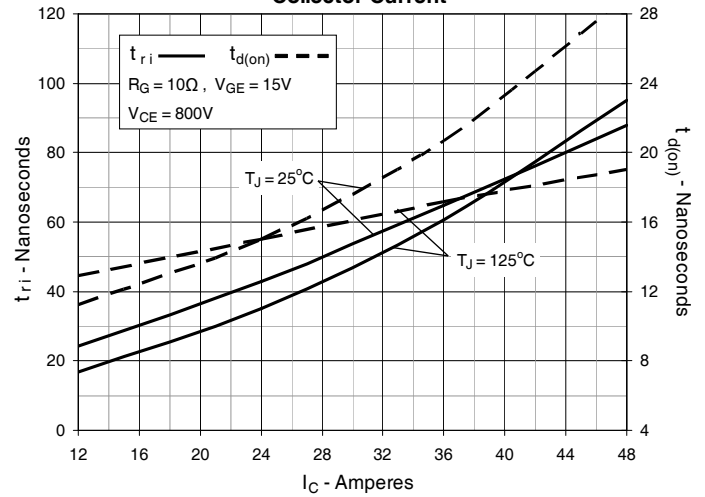
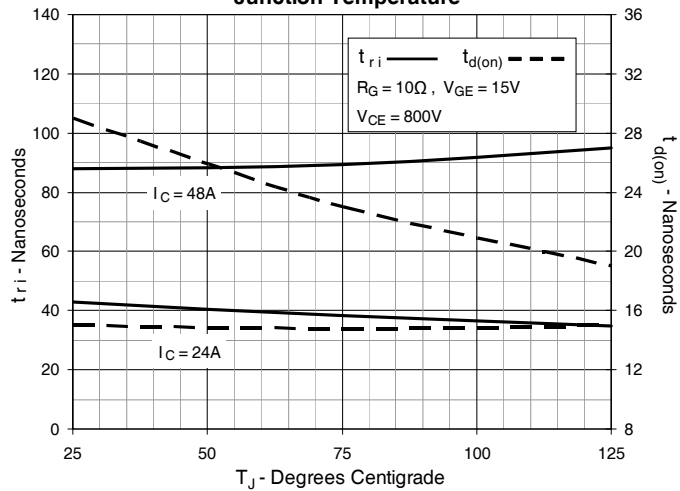
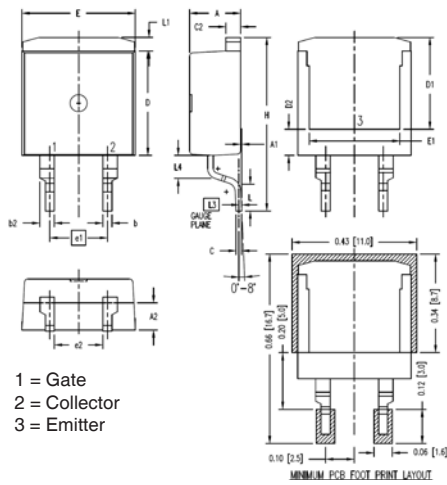
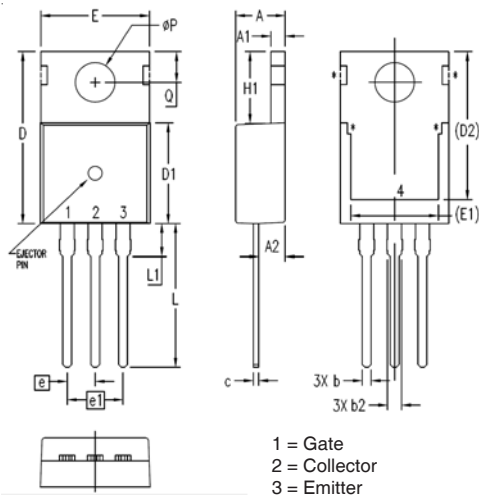


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature



TO-263HV Outline


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
D2	.083	.098	2.10	2.50
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200	BSC	5.08	BSC
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010	BSC	0.254	BSC
(L4)	.071	.087	1.80	2.20

TO-220 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100	BSC	2.54	BSC
e1	.200	BSC	5.08	BSC
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20



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